



TC 1700

Copy of #

) Before the Examiner:  
 ) Group Art Unit: 1741

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to the Assistant Commissioner for Patents, Washington, D.C. 20231 on:

February 12, 2003  
(Date of Deposit)  
Kenneth A. Gandy  
Name of Registered Representative  
Signature  
February 12, 2008  
Date of Signature

# METHOD AND APPARATUS FOR THE PREPARATION OF HIGH PURITY PHOSPHINE OR OTHER GAS

Assistant Commissioner for Patents  
Washington, DC 20231

This is in response to the Office Action dated November 12, 2002. Please provide any extensions of time that may be necessary and charge any fees that may be due, to Deposit Account No. 23-3030, but not to include the payment of any issue fees.

**Please add the following new claims.**

--32. (New) A chemical reactor system for generation of high purity gas for semiconductor fabrication, comprised of:

- a source of microwave radiation;
- a reaction chamber for receiving a precursor material for generating said gas,

said reaction chamber adapted to generate said gas under pressure;